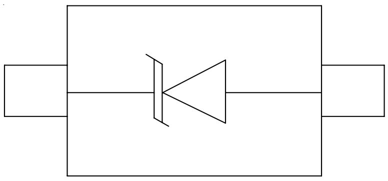
Description

The AR3301D5 is a uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3301D5 has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into a SOD-523 lead-free package. The small size, ultra-low capacitance and high ESD surge protection make AR3301D5 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- Ultra low capacitance: 0.6pF typical
- Ultra low leakage: nA level
- Operating voltage: 3.3V
- Low clamping voltage
- Complies with following standards:
  – IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±25kV
    Contact discharge: ±20kV
  – IEC61000-4-5 (Lightning) 6A (8/20μs)
- RoHS Compliant

Dimensions and Pin Configuration



Circuit and Pin Schematic

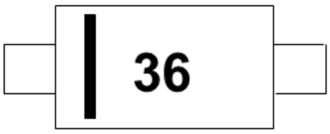
Mechanical Characteristics

- Package: SOD-523
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



36 : Device Marking Code
Bar denotes Cathode

Ordering Information

Part Number	Packaging	Reel Size
AR3301D5	3000/Tape & Reel	7 inch

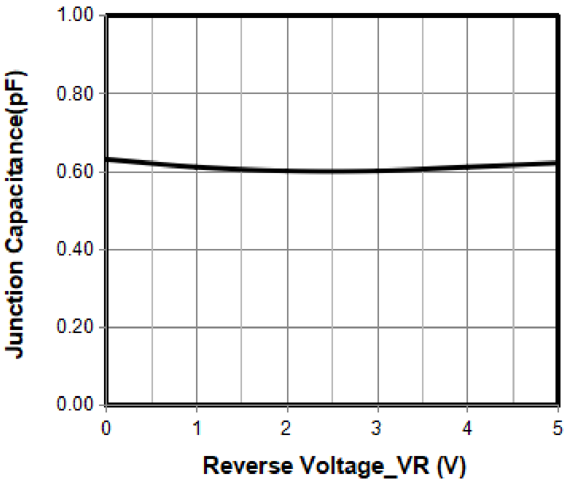
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	100	W
Peak Pulse Current (8/20μs)	I_{PP}	6	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

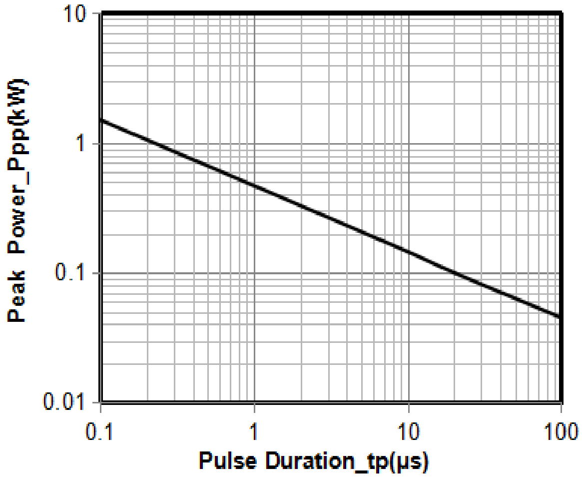
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	4. 2			V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 3.3V
Clamping Voltage	V_C			9	V	I_{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V_C			16	V	I_{PP} = 6A (8 x 20μs pulse)
Junction Capacitance	C_J		0.6		pF	VR = 0V, f = 1MHz

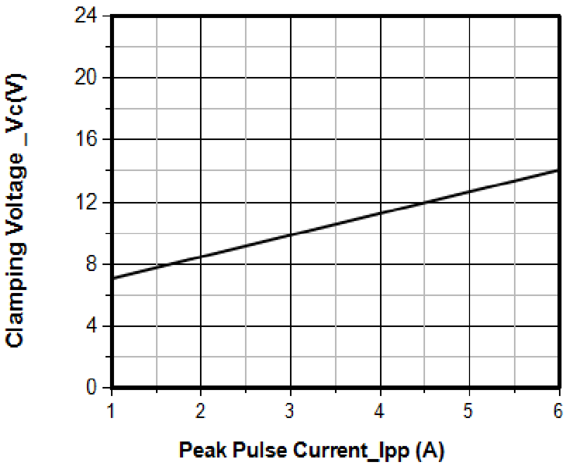
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



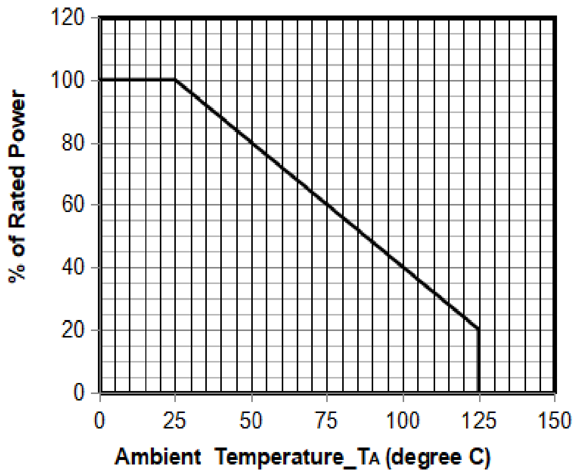
Junction Capacitance vs. Reverse Voltage



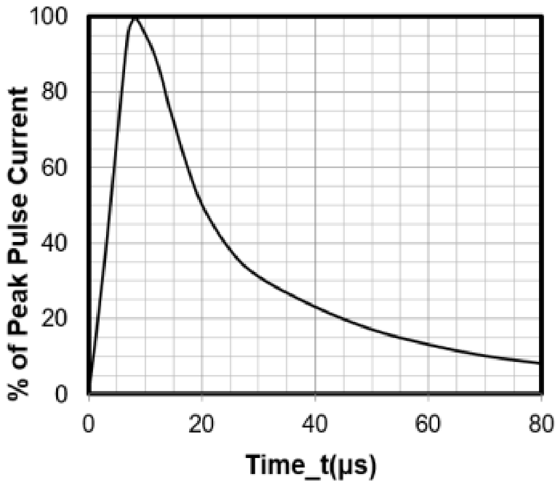
Peak Pulse Power vs. Pulse Time



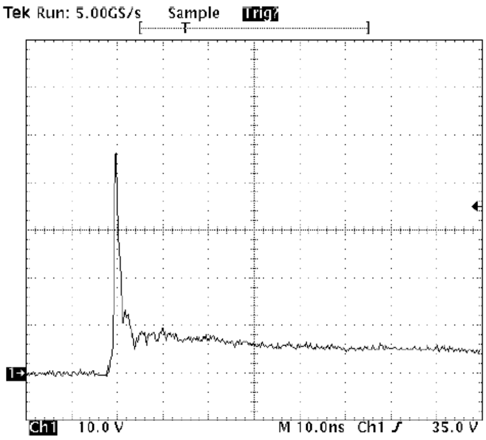
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

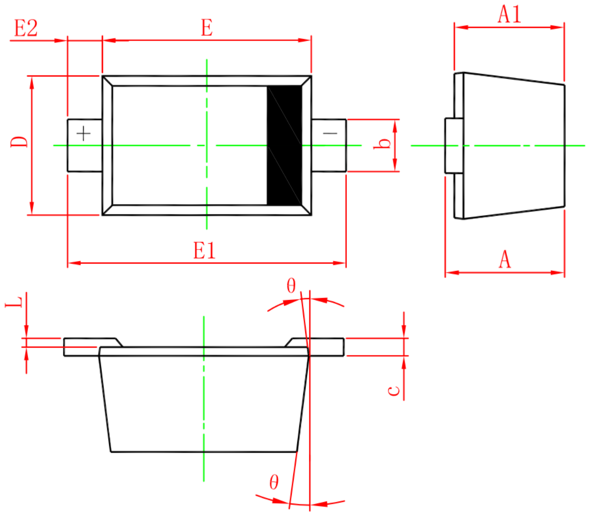


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

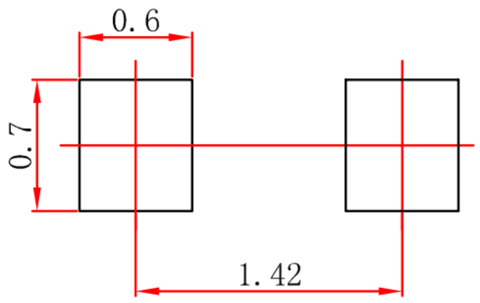
8 kV Contact per IEC61000−4−2

SOD-523 Package Outline Drawing



SY	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.51	- -	0.77	0.020	- -	0.031
A1	0.50	- -	0.70	0.020	- -	0.028
b	0.25	- -	0.35	0.010	- -	0.014
c	0.08	- -	0.15	0.003	- -	0.006
D	0.75	- -	0.85	0.030	- -	0.033
E	1.10	- -	1.30	0.043	- -	0.051
E1	1.50	- -	1.70	0.059		0.067
E2	0.20REF			0.008REF		
L	0.01	- -	0.07	0.001	- -	0.003
Θ	7° REF			7° REF		

Suggested Land Pattern



Unit： mm

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